

# SSM6J801R

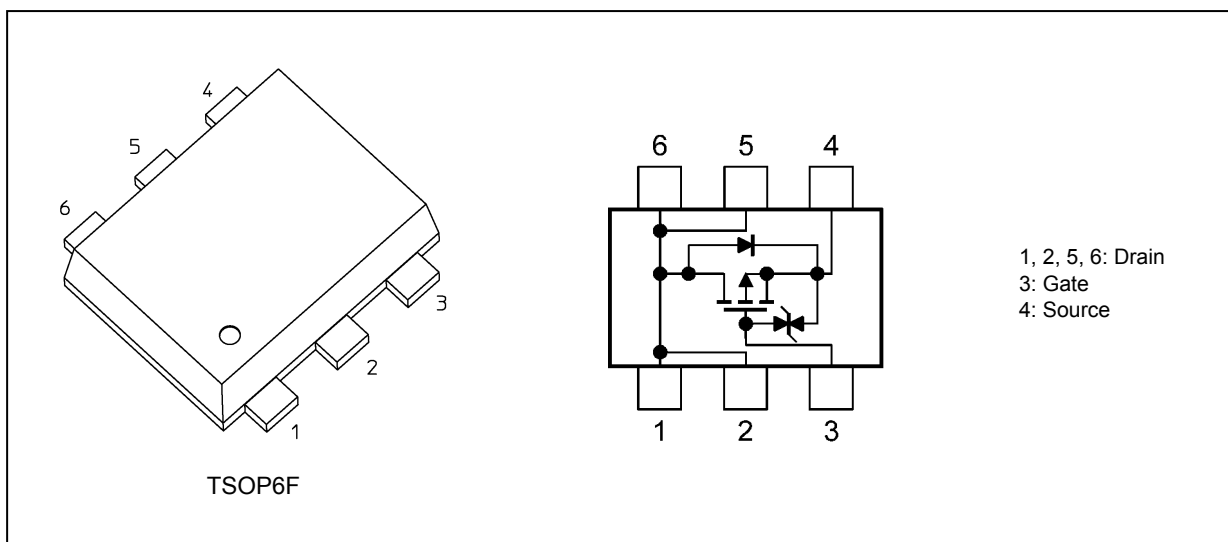
## 1. Applications

- Power Management Switches

## 2. Features

- (1) 1.5 V gate drive voltage.
- (2) Low drain-source on-resistance
  - :  $R_{DS(ON)} = 88.4 \text{ m}\Omega$  (max) (@ $V_{GS} = -1.5 \text{ V}$ )
  - $R_{DS(ON)} = 56.0 \text{ m}\Omega$  (max) (@ $V_{GS} = -1.8 \text{ V}$ )
  - $R_{DS(ON)} = 39.7 \text{ m}\Omega$  (max) (@ $V_{GS} = -2.5 \text{ V}$ )
  - $R_{DS(ON)} = 32.5 \text{ m}\Omega$  (max) (@ $V_{GS} = -4.5 \text{ V}$ )

## 3. Packaging and Pin Assignment



#### 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, $T_a = 25\text{ }^{\circ}\text{C}$ )

| Characteristics                              | Symbol    | Rating     | Unit               |
|----------------------------------------------|-----------|------------|--------------------|
| Drain-source voltage                         | $V_{DS}$  | -20        | V                  |
| Gate-source voltage                          | $V_{GS}$  | -8/+6      |                    |
| Drain current (DC) (Note 1)                  | $I_D$     | -6.0       | A                  |
| Drain current (pulsed) (Note 1), (Note 2)    | $I_{DP}$  | -24.0      |                    |
| Power dissipation (Note 3)                   | $P_D$     | 1.5        | W                  |
| Power dissipation $t = 10\text{ s}$ (Note 3) |           | 3.0        |                    |
| Channel temperature                          | $T_{ch}$  | 150        | $^{\circ}\text{C}$ |
| Storage temperature                          | $T_{stg}$ | -55 to 150 |                    |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Note 1: Ensure that the channel temperature does not exceed  $150\text{ }^{\circ}\text{C}$ .

Note 2: Pulse width (PW)  $\leq 10\text{ }\mu\text{s}$ , duty  $\leq 1\%$

Note 3: Device mounted on a  $25.4\text{ mm} \times 25.4\text{ mm} \times 1.6\text{ mm}$  FR4 glass epoxy board (Cu pad:  $645\text{ mm}^2$ )

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance,  $R_{th(ch-a)}$ , and the drain power dissipation,  $P_D$ , vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

## 5. Electrical Characteristics

### 5.1. Static Characteristics (Unless otherwise specified, $T_a = 25^\circ\text{C}$ )

| Characteristics                         | Symbol        | Test Condition                                      | Min  | Typ. | Max     | Unit             |
|-----------------------------------------|---------------|-----------------------------------------------------|------|------|---------|------------------|
| Gate leakage current                    | $I_{GSS}$     | $V_{DS} = 0\text{ V}$ , $V_{GS} = -8 / +6\text{ V}$ | —    | —    | $\pm 1$ | $\mu\text{A}$    |
| Drain cut-off current                   | $I_{DSS}$     | $V_{DS} = -20\text{ V}$ , $V_{GS} = 0\text{ V}$     | —    | —    | -1      |                  |
| Drain-source breakdown voltage          | $V_{(BR)DSS}$ | $I_D = -1\text{ mA}$ , $V_{GS} = 0\text{ V}$        | -20  | —    | —       | V                |
| Drain-source breakdown voltage (Note 1) | $V_{(BR)DSX}$ | $I_D = -1\text{ mA}$ , $V_{GS} = 5\text{ V}$        | -15  | —    | —       |                  |
| Gate threshold voltage (Note 2)         | $V_{th}$      | $V_{DS} = -3\text{ V}$ , $I_D = -1\text{ mA}$       | -0.3 | —    | -1.0    |                  |
| Drain-source on-resistance (Note 3)     | $R_{DS(ON)}$  | $I_D = -3.0\text{ A}$ , $V_{GS} = -4.5\text{ V}$    | —    | 24.9 | 32.5    | $\text{m}\Omega$ |
|                                         |               | $I_D = -2.5\text{ A}$ , $V_{GS} = -2.5\text{ V}$    | —    | 31.1 | 39.7    |                  |
|                                         |               | $I_D = -1.5\text{ A}$ , $V_{GS} = -1.8\text{ V}$    | —    | 38.8 | 56.0    |                  |
|                                         |               | $I_D = -0.5\text{ A}$ , $V_{GS} = -1.5\text{ V}$    | —    | 47.4 | 88.4    |                  |
| Forward transfer admittance (Note 3)    | $ Y_{fs} $    | $V_{DS} = -3\text{ V}$ , $I_D = -1.0\text{ A}$      | 4.5  | 9.1  | —       | S                |

Note 1: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current ( $I_D$ ) to below (-1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ .

Take this into consideration when using the device.

Note 3: Pulse measurement.

### 5.2. Dynamic Characteristics (Unless otherwise specified, $T_a = 25^\circ\text{C}$ )

| Characteristics                | Symbol    | Test Condition                                                                                                   | Min | Typ. | Max | Unit        |
|--------------------------------|-----------|------------------------------------------------------------------------------------------------------------------|-----|------|-----|-------------|
| Input capacitance              | $C_{iss}$ | $V_{DS} = -10\text{ V}$ , $V_{GS} = 0\text{ V}$ ,<br>$f = 1\text{ MHz}$                                          | —   | 840  | —   | $\text{pF}$ |
| Reverse transfer capacitance   | $C_{rss}$ |                                                                                                                  | —   | 99   | —   |             |
| Output capacitance             | $C_{oss}$ |                                                                                                                  | —   | 118  | —   |             |
| Switching time (turn-on time)  | $t_{on}$  | $V_{DD} = -10\text{ V}$ , $I_D = -2.0\text{ A}$ ,<br>$V_{GS} = 0$ to $-2.5\text{ V}$ , $R_G = 4.7\text{ }\Omega$ | —   | 32   | —   | ns          |
| Switching time (turn-off time) | $t_{off}$ |                                                                                                                  | —   | 107  | —   |             |

### 5.3. Switching Time Test Circuit

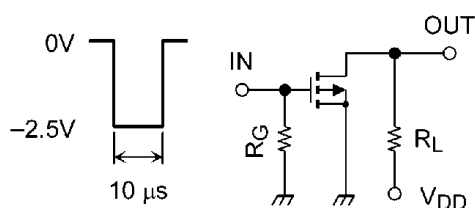


Fig. 5.3.1 Switching Time Test Circuit

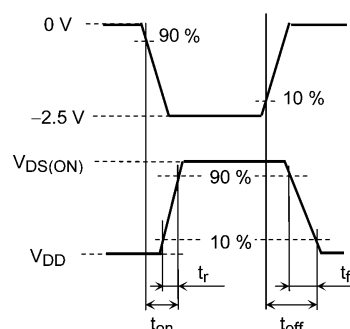


Fig. 5.3.2 Input Waveform/Output Waveform

### 5.4. Gate Charge Characteristics (Unless otherwise specified, $T_a = 25^\circ\text{C}$ )

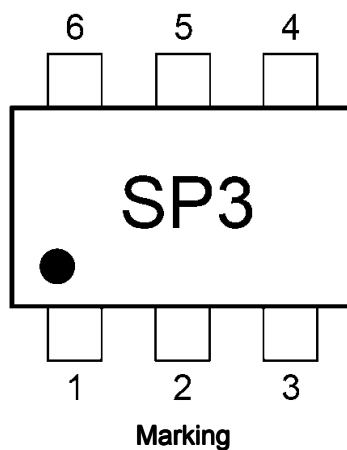
| Characteristics                                 | Symbol    | Test Condition                                                                | Min | Typ. | Max | Unit |
|-------------------------------------------------|-----------|-------------------------------------------------------------------------------|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | $Q_g$     | $V_{DD} = -10\text{ V}$ , $I_D = -4.0\text{ A}$ ,<br>$V_{GS} = -4.5\text{ V}$ | —   | 12.8 | —   | nC   |
| Gate-source charge 1                            | $Q_{gs1}$ |                                                                               | —   | 1.4  | —   |      |
| Gate-drain charge                               | $Q_{gd}$  |                                                                               | —   | 3.0  | —   |      |

### 5.5. Source-Drain Characteristics (Unless otherwise specified, $T_a = 25\text{ }^{\circ}\text{C}$ )

| Characteristics                | Symbol    | Test Condition       | Min | Typ. | Max | Unit |
|--------------------------------|-----------|----------------------|-----|------|-----|------|
| Diode forward voltage (Note 1) | $V_{DSF}$ | $I_D = 6.0\text{ A}$ | —   | 0.87 | 1.2 | V    |

Note 1: Pulse measurement.

### 6. Marking



# 7. Characteristics Curves (Note)

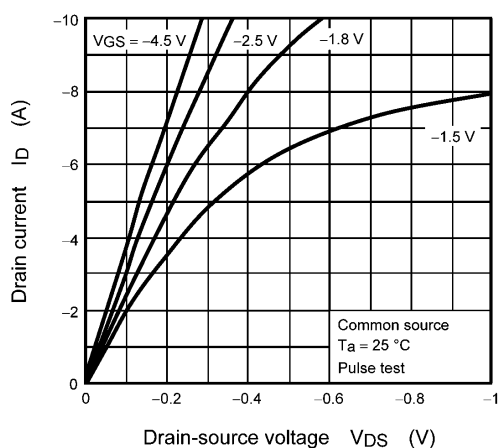


Fig. 7.1  $I_D - V_{DS}$

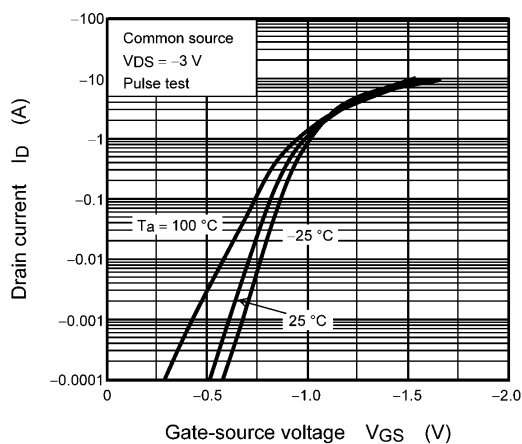


Fig. 7.2  $I_D - V_{GS}$

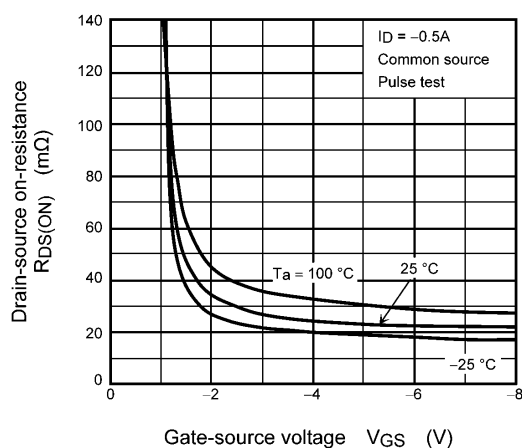


Fig. 7.3  $R_{DS(ON)} - V_{GS}$

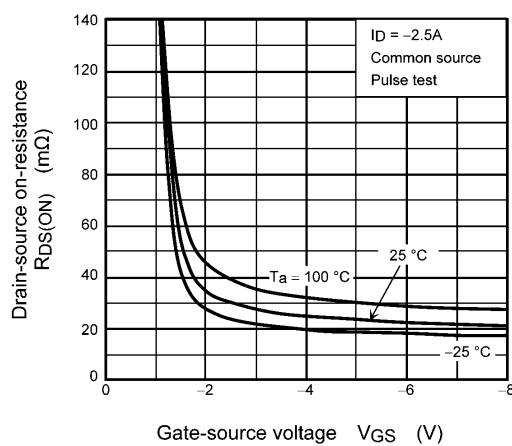


Fig. 7.4  $R_{DS(ON)} - V_{GS}$

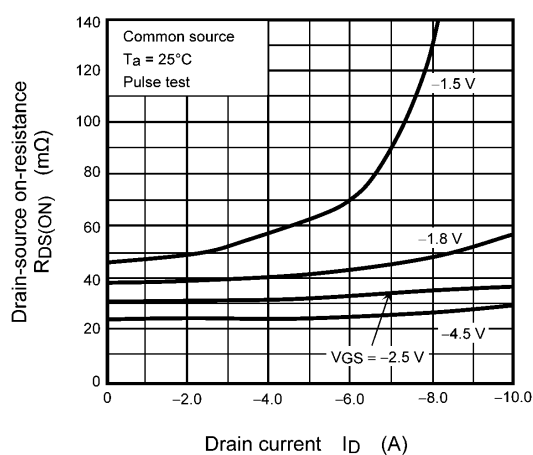


Fig. 7.5  $R_{DS(ON)} - I_D$

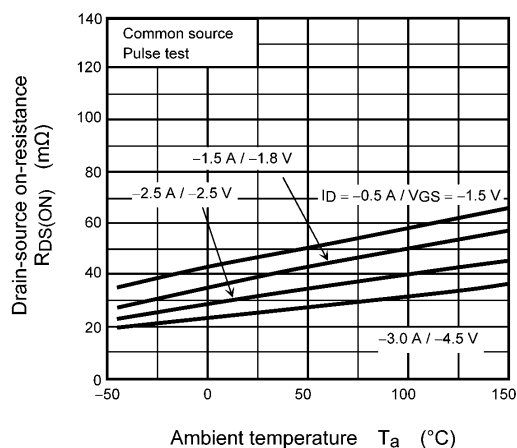


Fig. 7.6  $R_{DS(ON)} - T_a$

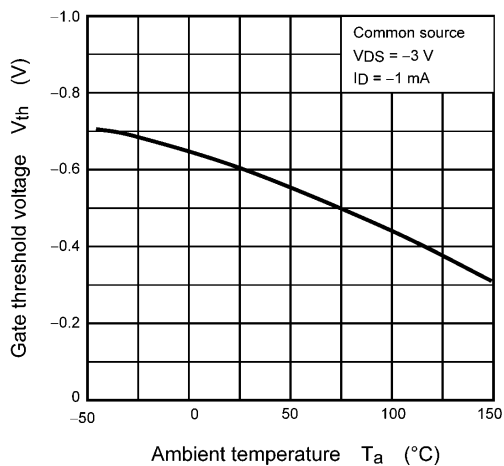


Fig. 7.7  $V_{th} - T_a$

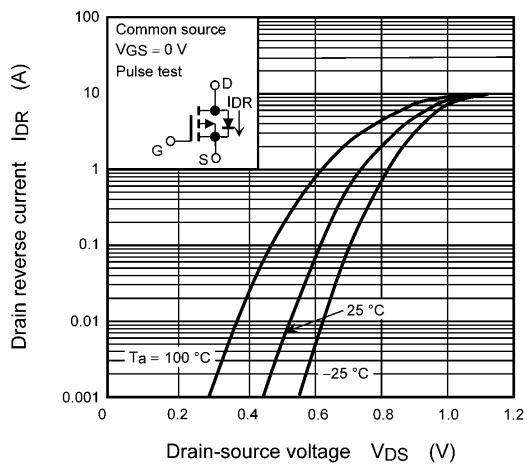


Fig. 7.8  $I_{DR} - V_{DS}$

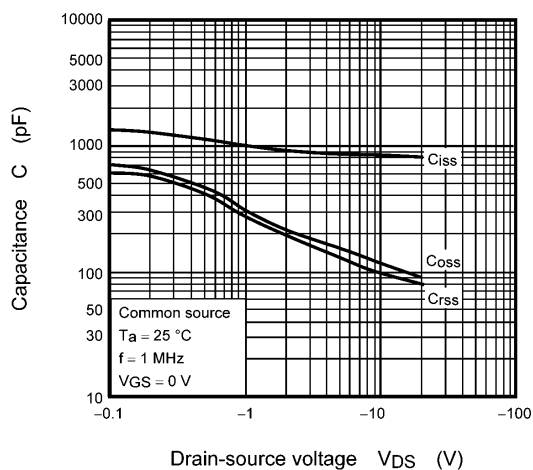


Fig. 7.9  $C - V_{DS}$

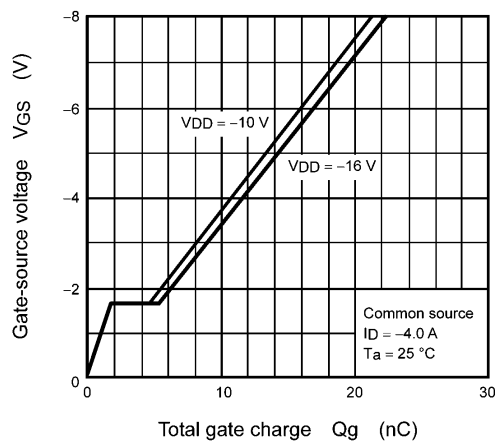


Fig. 7.10 Dynamic Input Characteristics

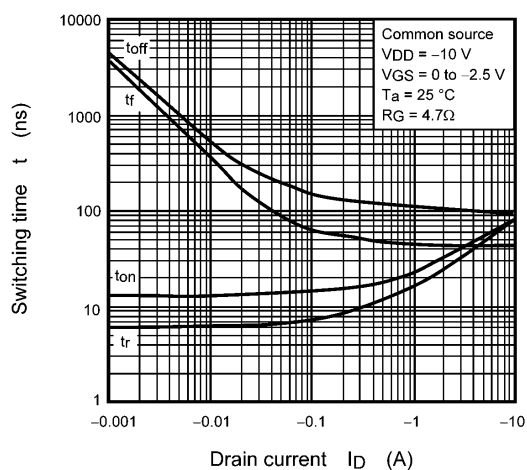


Fig. 7.11  $t - I_D$

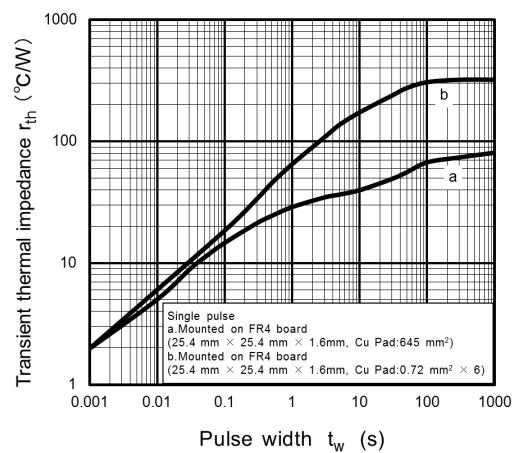
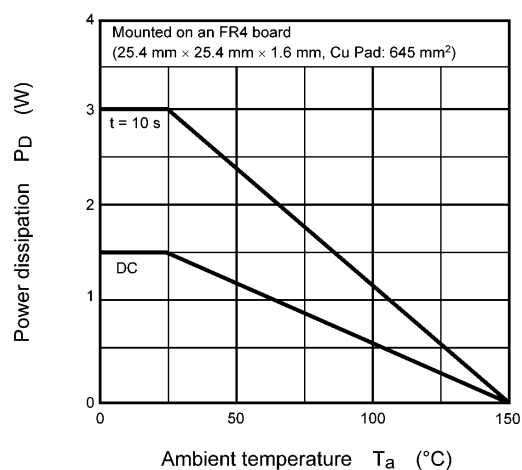
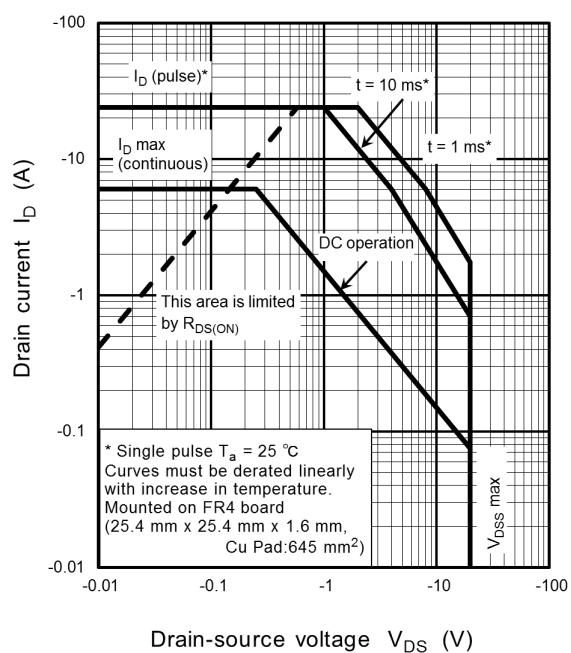


Fig. 7.12  $r_{th} - t_w$



**Fig. 7.13  $P_D - T_a$**

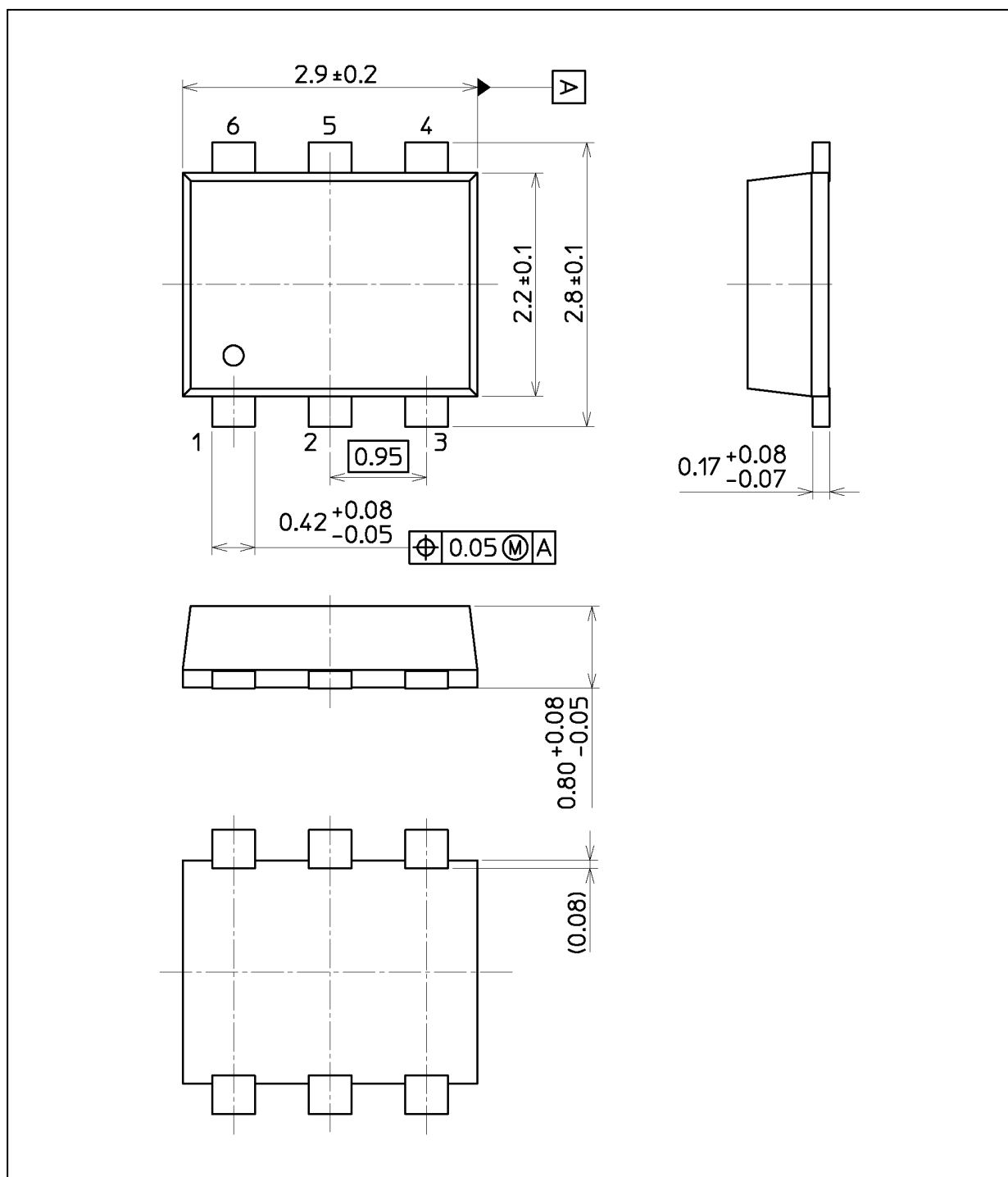


**Fig. 7.14 Safe Operating Area**

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

## Package Dimensions

Unit: mm



Weight: 0.016 g (typ.)

| Package Name(s)  |
|------------------|
| Nickname: TSOP6F |

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